

Vishay Siliconix

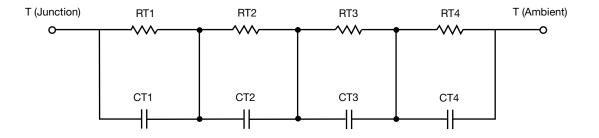
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION THERMAL RESISTANCE (°C/W)					
RT1	192.3210	N/A	N/A		
RT2	61.5014	N/A	N/A		
RT3	320.4035	N/A	N/A		
RT4	97.9177	N/A	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	1.1215m	N/A	N/A		
CT2	161.6800u	N/A	N/A		
CT3	4.1548m	N/A	N/A		
CT4	137.6692m	N/A	N/A		

Note

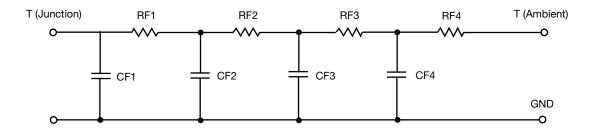
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



Vishay Siliconix

R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	84.0820	N/A	N/A		
RF2	316.9083	N/A	N/A		
RF3	190.5895	N/A	N/A		
RF4	80.2209	N/A	N/A		
	THERMAL CAPACIT	ANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	137.1307u	N/A	N/A		
CF2	856.4602u	N/A	N/A		
CF3	6.1949m	N/A	N/A		
CF4	134.1221m	N/A	N/A		

Note

• n/a indicates not applicable



Si1023CX-GE3_RC

Vishay Siliconix

